

High Voltage MOSFET

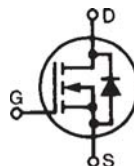
N-Channel, Depletion Mode

IXTH 10N100D IXTT 10N100D

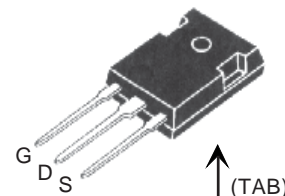
$$V_{DSS} = 1000 \text{ V}$$

$$I_{D25} = 10 \text{ A}$$

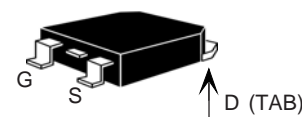
$$R_{DS(on)} = 1.4 \text{ } \Omega$$



TO-247 (IXTH)



TO-268 (IXTT)



G = Gate D = Drain
S = Source TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSX}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	1000	V
V_{DGX}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	1000	V
V_{GS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	10	A
I_{DM}	$T_C = 25^\circ\text{C}$; pulse width limited by T_{JM}	20	A
P_D	$T_C = 25^\circ\text{C}$	400	W
T_J		-55 ... + 150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... + 150	$^\circ\text{C}$
T_L	1.6 mm (0.063 in) from case for 10 seconds	300	$^\circ\text{C}$
T_{ISOL}	Plastic case for 10 seconds	300	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	4	g

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSX}	$V_{GS} = -10 \text{ V}$, $I_D = 250 \text{ } \mu\text{A}$	1000		V
$V_{GS(off)}$	$V_{DS} = 25 \text{ V}$, $I_D = 250 \text{ } \mu\text{A}$	-1.5		V
I_{GSS}	$V_{GS} = \pm 30 V_{DC}$, $V_{DS} = 0$			$\pm 100 \text{ nA}$
$I_{DSX(off)}$	$V_{DS} = V_{DSS}$ $V_{GS} = -10 \text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		25 μA
				500 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 10 \text{ A}$ Note 1			1.4 Ω
$I_{D(on)}$	$V_{GS} = 0 \text{ V}$, $V_{DS} = 25 \text{ V}$ Note 1		1.0	A

Features

- Normally ON Mode
- International standard packages
- Molding epoxies meet UL 94 V-0 flammability classification

Applications

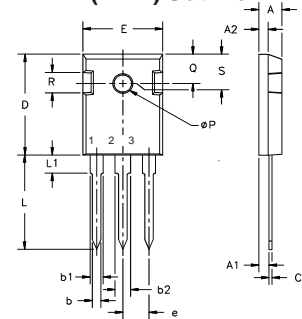
- Level shifting
- Triggers
- Solid State Relays
- Current Regulators
- Active load

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 30\text{ V}$, $I_D = 10\text{ A}$, Note 1	3.0	5.4	S
C_{iss}	$V_{GS} = -10\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$		2500	pF
C_{oss}			300	pF
C_{rss}			100	pF
$t_{d(on)}$	$V_{GS} = 0\text{ V to } -10\text{ V}$, $V_{DS} = 0.5 \cdot V_{DSX}$ $I_D = 10\text{ A}$, $R_G = 4.7\ \Omega$ (External),		35	ns
t_r			85	ns
$t_{d(off)}$			110	ns
t_f			75	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 \cdot V_{DSX}$, $I_D = 0.5 \cdot I_{D25}$		130	nC
Q_{gs}			27	nC
Q_{gd}			58	nC
R_{thJC}			0.31	K/W
R_{thCK}		0.25		K/W

Source-Drain Diode

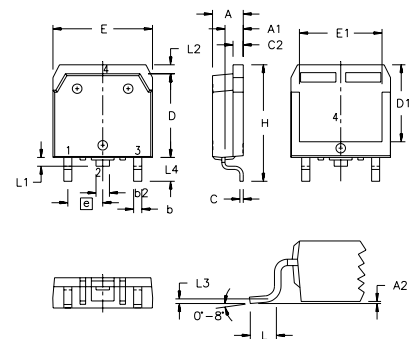
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{SD}	$I_F = I_{D25}$, $V_{GS} = -10\text{ V}$, Note 1		1.1	1.5 V
t_{rr}	$I_F = 20\text{ A}$, $-di/dt = 100\text{ A}/\mu\text{s}$, $V_R = 100\text{ V}$ $V_{GS} = -10\text{ V}$		850	ns

Note 1: Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$

TO-247 AD (IXTH) Outline


Terminals:
 1 - Gate 2 - Drain
 3 - Source Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.088
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L ₁		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-268 (IXTTH) Outline


Terminals:
 1 - Gate 2 - Drain
 3 - Source Tab - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A ₁	.106	.114	2.70	2.90
A ₂	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b ₂	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C ₂	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D ₁	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E ₁	.524	.535	13.30	13.60
e	.215	BSC	5.45	BSC
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L ₁	.047	.055	1.20	1.40
L ₂	.039	.045	1.00	1.15
L ₃	.010	BSC	0.25	BSC
L ₄	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065B1	6,683,344	6,727,585
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123B1	6,534,343	6,710,405B2	6,759,692
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478B2

Fig. 1. Output Characteristics @ 25°C

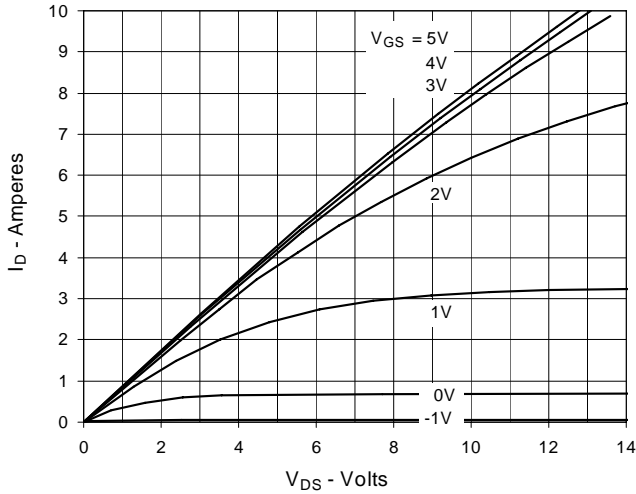


Fig. 2. Extended Output Characteristics @ 25°C

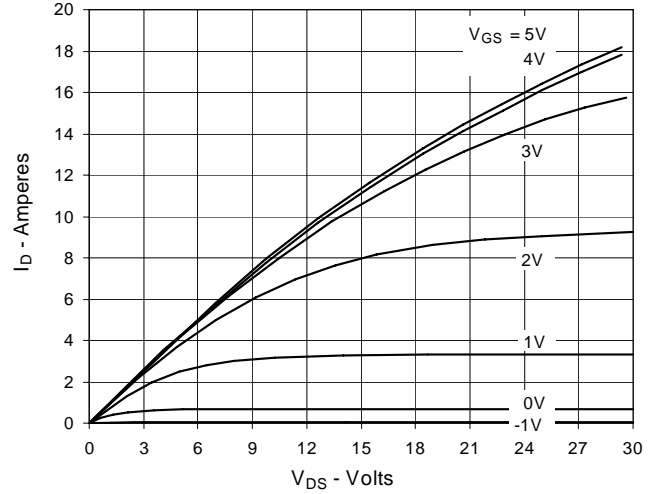


Fig. 3. Output Characteristics @ 125°C

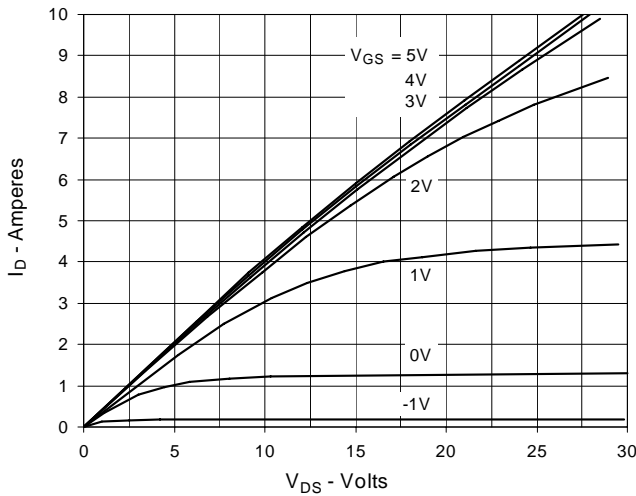


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 5A$ Value vs. Junction Temperature

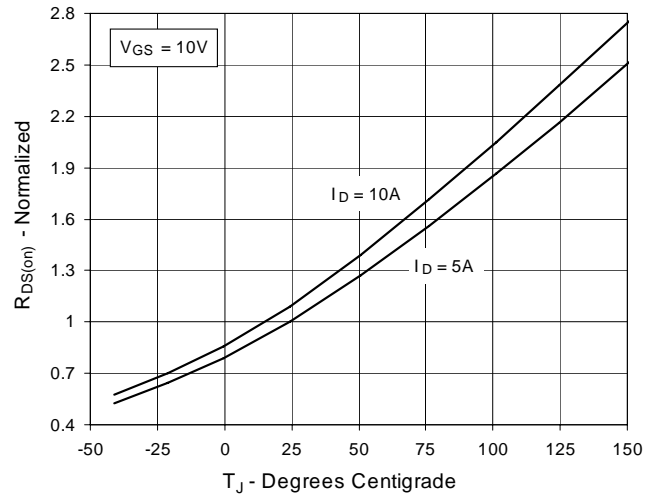


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 5A$ Value vs. Drain Current

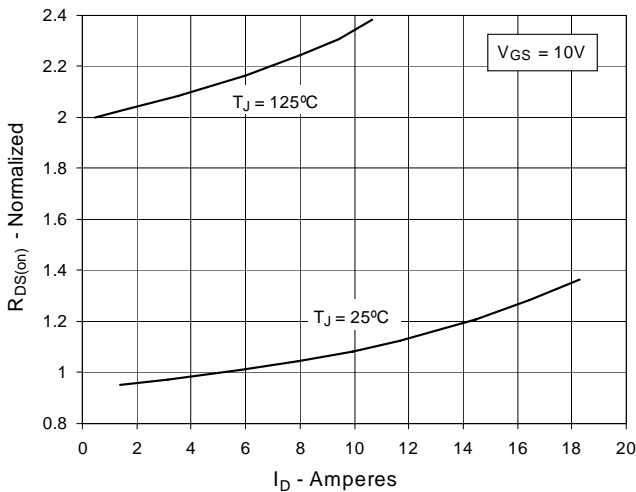


Fig. 6. Maximum Drain Current vs. Case Temperature

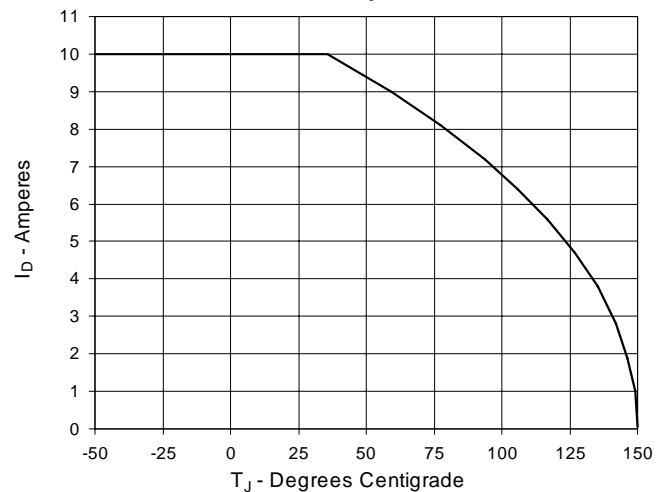


Fig. 7. Input Admittance

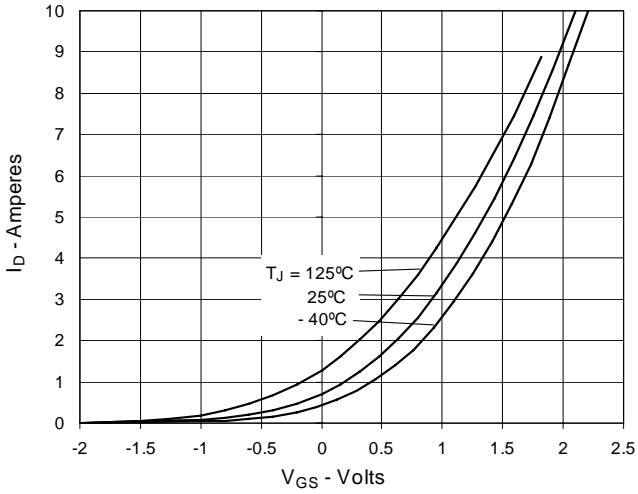


Fig. 8. Transconductance

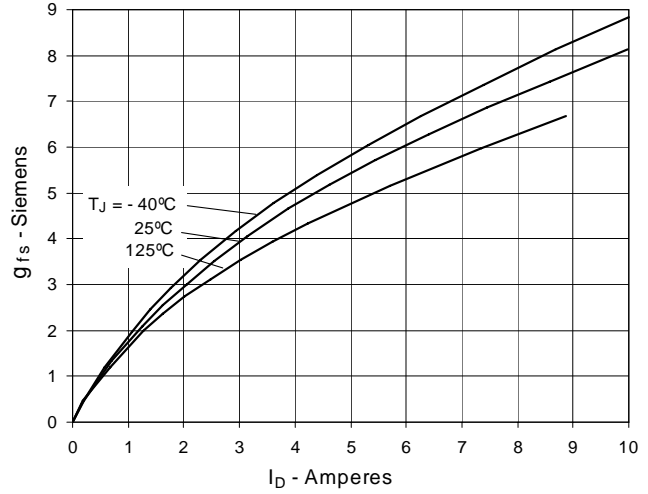


Fig. 9. Forward Voltage Drop of Intrinsic Diode

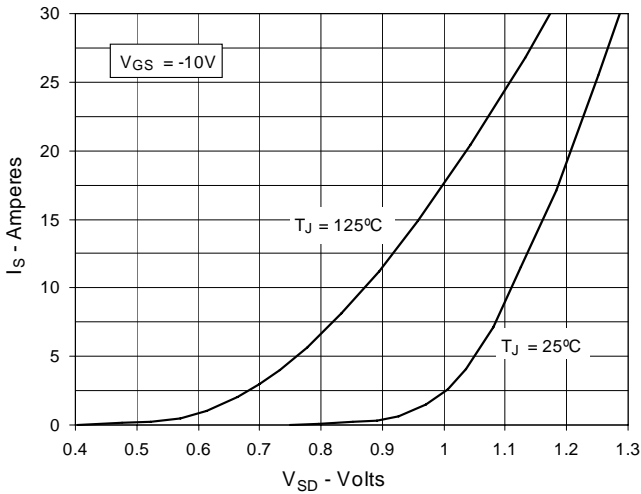


Fig. 10. Breakdown & Threshold Voltages vs. Junction Temperature

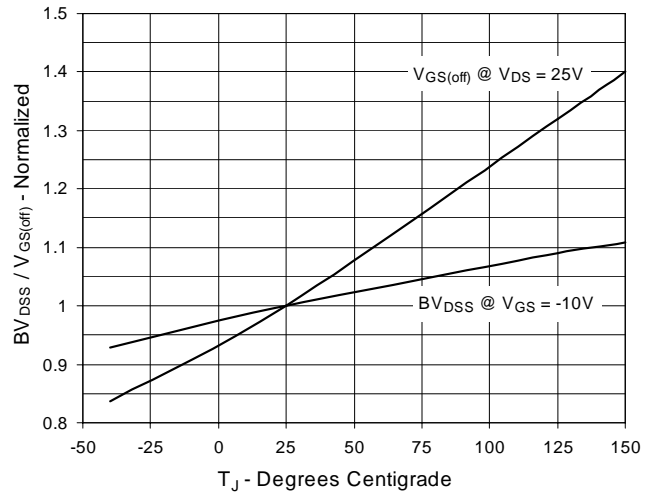


Fig. 11. Gate Charge

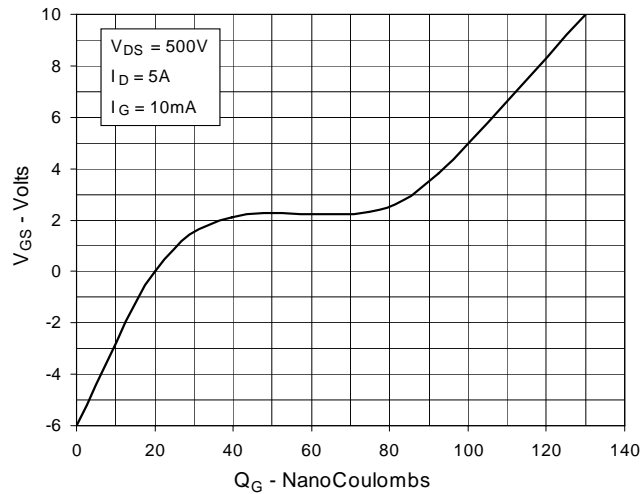


Fig. 12. Capacitance

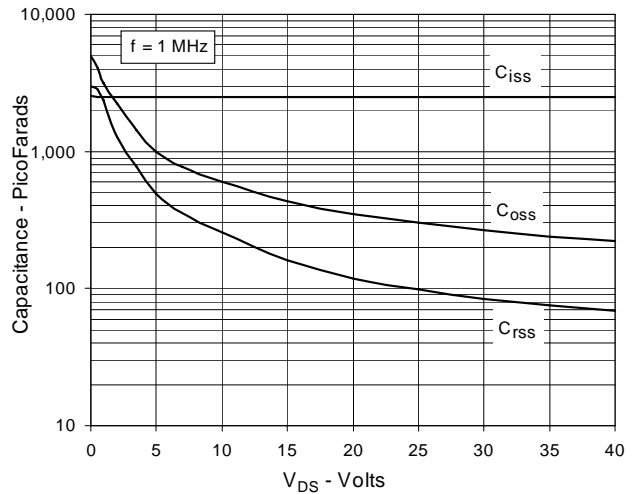


Fig. 13. Maximum Transient Thermal Resistance

